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U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10081842	02/25/2002	257420	698	2815	LAM

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****CONTINUING DATA VERIFIED:** N

**** FOREIGN APPLICATIONS VERIFIED:** Y
JAPAN JP2001-52351 02/27/2001

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PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no		57810-031
Verified and Acknowledged Examiners's initials		
TITLE : Nitride-based semiconductor element and method of forming nitride-based semiconductor		
U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)		

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg.
		Print Fig.	
<input type="checkbox"/> TERMINAL		Primary Examiner	
DISCLAIMER		Application Examiner	
		PREPARED FOR ISSUE	
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